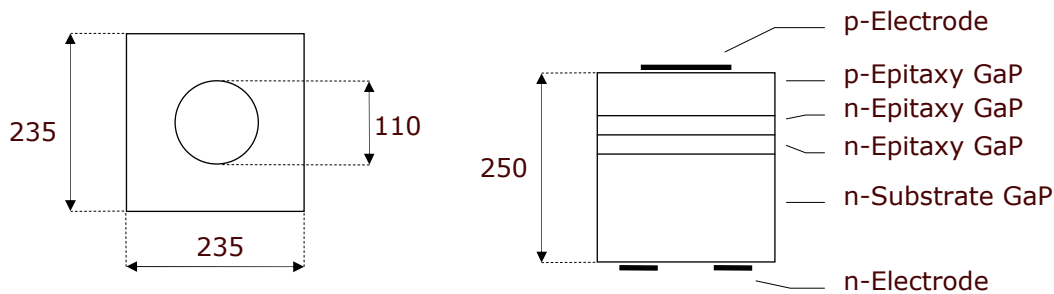


**YELLOW**

**Item No.: 170622**

1. This specification applies to GaAsP / GaP LED Chips
2. Structure
  - 2.1 Mesa structure
  - 2.2 Electrodes
 

p-side (anode)	Au alloy
n-side (cathode)	Au alloy
3. Outlines (dimensions in microns)



Wire bond contacts can also be square

4. Electrical and optical characteristics (T=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Forward voltage	$V_F$	$I_F = 2 \text{ mA}$		1,85	2,05	V
Reverse current	$I_R$	$V_R = 5 \text{ V}$			10	$\mu\text{A}$
Luminous intensity *	$I_V$	$I_F = 2 \text{ mA}$	180	300		$\mu\text{cd}$
dom. wavelength	$\lambda_D$	$I_F = 2 \text{ mA}$		590		nm

\* On request, wafers will be delivered according to luminous intensity classes  
Brightness measurement at OSA on gold plate

5. Packing

Dice on adhesive film with 1) wire bond side on top  
2) back contact on top

6. Labeling

Type	Lot No.	$I_V$ typ min max	Quantity